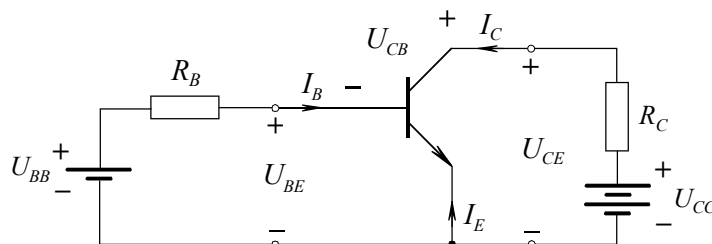


Written exam at the course  
**ELEMENTS of SEMICONDUCTOR ELECTRONICS**  
**(ELEMENTI POLPREVODNIŠKE ELEKTRONIKE)**  
 1<sup>st</sup> Bologna grade – 2<sup>nd</sup> year – Electronics – AE  
 30. 1. 2015

1. Determine semiconductor type for a sample/piece of crystalline Si which contains homogeneously distributed donor impurities at a concentration of  $1,5 \times 10^{17} \text{ cm}^{-3}$ . Calculate the energy difference (in eV) between the actual and intrinsic Fermi level at a temperature of 340 K and sketch energy band diagram. Calculate the specific conductivity of the sample.  
 (Data:  $n_i = 2,5 \times 10^{11} \text{ cm}^{-3}$ ,  $\mu_n = 800 \text{ cm}^2(\text{Vs})^{-1}$ ,  $\mu_p = 320 \text{ cm}^2(\text{Vs})^{-1}$ )  
**(Solution: n-type,  $U_T = 29,33 \text{ mV}$ ;  $E_F - E_{Fi} = 0,390 \text{ eV}$ ;  $\sigma = 19,2 \text{ S/cm}$ )**

2. For the diode with a quality factor of  $n = 1,9$  at room temperature we measured the following two points of the characteristic:
- $I_1 = 1 \text{ mA}$  at  $U_1 = 0,62 \text{ V}$
  - $I_2 = 50 \text{ mA}$  at  $U_2 = 0,89 \text{ V}$
- Calculate the diode's saturation current, disregarding the influence of the internal resistance in the first point. Afterwards calculate the internal resistance.  
**(Solution:  $I_S = 3 \text{ nA}$ ;  $U_{D2} = 0,811 \text{ V}$ ;  $R_S = 1,86 \Omega$ )**

3. In the given circuit with a bipolar transistor determine the base resistance  $R_B$  so that the voltage on the collector resistor  $R_C$  equals  $U_{CC}/2$ . In which range the transistor operates (explain why)?  
 (Data:  $\alpha_F = 0,99$ ,  $U_{BB} = 5 \text{ V}$ ,  $U_{CC} = 12 \text{ V}$ ,  $R_C = 2,2 \text{ k}\Omega$ ,  $U_{BE} \approx 0,7 \text{ V}$ ).



**(Solution:  $I_C = 2,73 \text{ mA}$ ;  $\beta = 99$ ;  $I_B = 27,6 \mu\text{A}$ ;  $R_B = 156 \text{ k}\Omega$ ;  $U_{CB} > 0 \Rightarrow$  active range)**

4. For a MOS transistor with an induced  $n$ -channel, which operates in the point  $U_{GS} = 5 \text{ V}$ ,  $U_{DS} = 5 \text{ V}$ , in common source orientation, determine the operating range (under-saturation or saturation) and incremental conduction quadripole parameters  $g_{ij}$ . Draw a replacement model of the transistor for small low-frequency signals in the given operating range (model with  $g$  parameters).  
 (Data:  $C_0 \mu_n = 1 \text{ mA/V}^2$ ,  $W/L = 0,8$ ,  $U_T = 1,2 \text{ V}$ )  
**(Solution: saturation;  $g_{11} = 0$ ;  $g_{12} = 0$ ;  $g_{21} = 3,04 \text{ mS}$ ;  $g_{22} = 0$ )**

You have 60 minutes, you are allowed to use the sheet with basic formulas and constants.  
 The results are expected to be published on Monday morning in the STUDIS.